



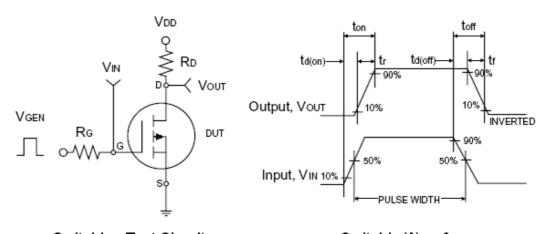
### 20V Dual N-Channel MOSFET w/ESD Protected

**Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit			
Static									
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	20			V			
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.6	0.8	1.0	V			
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I <sub>GSS</sub>			±10	uA			
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	uA			
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I <sub>D(ON)</sub>	30			Α			
Drain Course On State Besistance	$V_{GS} = 4.5V, I_D = 6.5A$			15	22	mΩ			
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 5.5A$	R <sub>DS(ON)</sub>		20	29				
Forward Transconductance	$V_{DS} = 10V, I_D = 6.5A$	<b>g</b> fs	1	30		S			
Diode Forward Voltage	$I_S = 1.7A, V_{GS} = 0V$	$V_{SD}$	1	0.6	1.2	V			
Dynamic <sup>b</sup>									
Total Gate Charge	$V_{DS} = 10V, I_{D} = 6.5A,$ $V_{GS} = 4.5V$	$Q_g$		15	20	nC			
Gate-Source Charge		$Q_gs$		3.4					
Gate-Drain Charge	V <sub>GS</sub> = 4.5 V	$Q_gd$		1.2					
Input Capacitance	10)/ )/ 0)/	$C_{iss}$		950		pF			
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$	$C_{oss}$		450					
Reverse Transfer Capacitance	f = 1.0MHz	$C_{rss}$	-	135					
Switching <sup>c</sup>									
Turn-On Delay Time	$V_{DD} = 10V, R_L = 10\Omega,$	t <sub>d(on)</sub>	-	140	200	nS			
Turn-On Rise Time		t <sub>r</sub>		210	250				
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 4.5V,$	t <sub>d(off)</sub>		3700	4800				
Turn-Off Fall Time	$R_{G} = 6\Omega$	t <sub>f</sub>		2000	2600				

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
  b. For DESIGN AID ONLY, not subject to production testing.
  b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

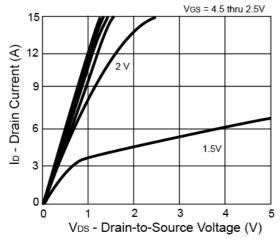




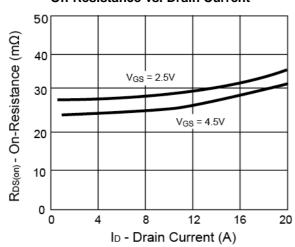
## 20V Dual N-Channel MOSFET w/ESD Protected

### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

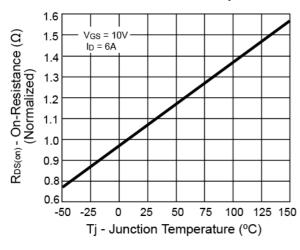




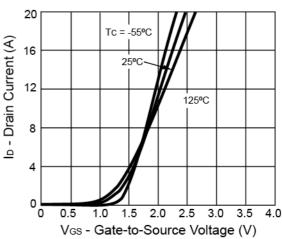
#### On-Resistance vs. Drain Current



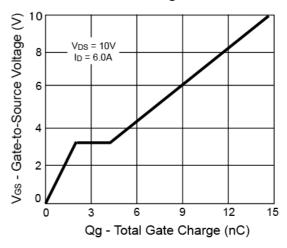
On-Resistance vs. Junction Temperature



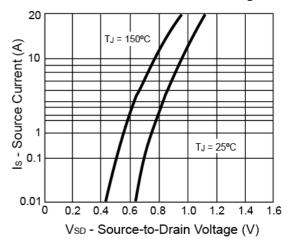
#### **Transfer Characteristics**



#### **Gate Charge**



#### **Source-Drain Diode Forward Voltage**



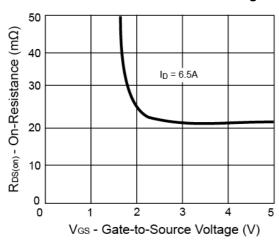


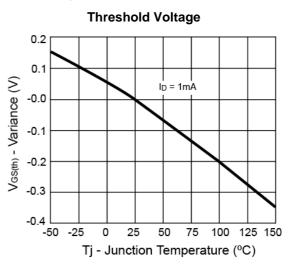


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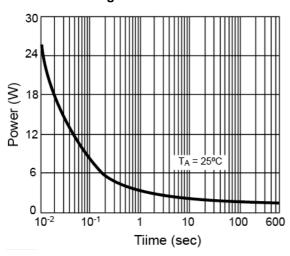
#### **Electrical Characteristics Curve** (Ta = 25°C, unless otherwise noted)

#### On-Resistance vs. Gate-Source Voltage

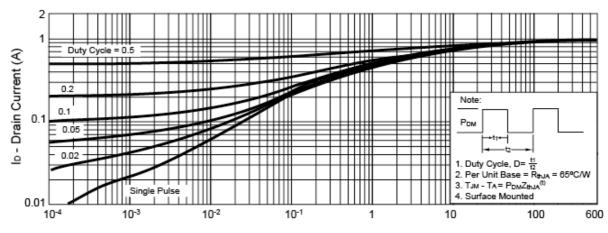




#### Single Pulse Power



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



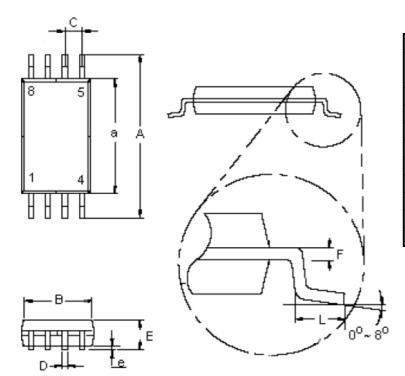
Square Wave Pulse Duration (sec)





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# **TSSOP-8 Mechanical Drawing**



TSSOP-8 DIMENSION							
DIM	MILLIMETERS		INCHES				
	MIN	MAX	MIN	MAX			
Α	6.20	6.60	0.244	0.260			
а	4.30	4.50	0.170	0.177			
В	2.90	3.10	0.114	0.122			
C	0.65 (typ)		0.025 (typ)				
D	0.25	0.30	0.010	0.019			
ш	1.05	1.20	0.041	0.049			
е	0.05	0.15	0.002	0.009			
F	0.127		0.005				
L	0.50	0.70	0.020	0.028			

## **Marking Diagram**



Y = Year Code

**M** = Month Code for Halogen Free Product

P =Feb Q =Mar O =Jan R =Apr

**S** =May **T** =Jun **U** =Jul V =Aug W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



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